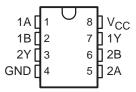
SN74LVC2G38 **DUAL 2-INPUT NAND GATE** WITH OPEN DRAIN OUTP

SCES554A - MARCH 2004 - REVISED OCTOBER 2004

- **Available in the Texas Instruments** NanoStar™ and NanoFree™ Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max tpd of 4 ns at 3.3 V
- Low Power Consumption, 10-µA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OI P} (Output Ground Bounce) <0.8 V at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) >2 V at V_{CC} = 3.3 V, T_A = 25°C
- **Ioff Supports Partial-Power-Down Mode** Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- **ESD Protection Exceeds JESD 22**
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DCT OR DCU PACKAGE (TOP VIEW)



YEP OR YZP PACKAGE (BOTTOM VIEW)

GND	04	50	2A
2Y	○3	6 O 7 O	2B
1B	O 2	70	1Y
1A	O 1	80	Vcc

description/ordering information

The SN74LVC2G38 is designed for 1.65-V to 5.5-V V_{CC} operation.

This device is a dual two-input NAND buffer gate with open-drain outputs. It performs the Boolean function $Y = A \bullet B$ or Y = A + B in positive logic.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

ORDERING INFORMATION

TA	PACKAGET	PACKAGE [†]			
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	B 1 (0000	SN74LVC2G38YEPR		
40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Reel of 3000	SN74LVC2G38YZPR	D7	
	SSOP - DCT	Reel of 3000	SN74LVC2G38DCTR	C38	
	VCCOR DOLL	Reel of 3000	SN74LVC2G38DCUR	020	
	VSSOP – DCU	Reel of 250	SN74LVC2G38DCUT	C38_	

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site. DCU: The actual top-side marking has one additional character that designates the assembly/test site. YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition $(1 = SnPb, \bullet = Pb-free).$



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoStar and NanoFree are trademarks of Texas Instruments.

SCES554A - MARCH 2004 - REVISED OCTOBER 2004

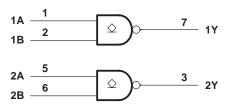
description/ordering information (continued)

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE (each gate)

INP	UTS	OUTPUT
Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
(see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	\dots -0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DCT package	220°C/W
DCU package	
YEP/YZP package	
Storage temperature range, T _{stq}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. The value of V_{CC} is provided in the recommended operating conditions table.
- 3. The package thermal impedance is calculated in accordance with JESD 51-7.



recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
.,	Complements	Operating	1.65	5.5	V
VCC	Supply voltage	Data retention only	1.5		V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		
.,		V _{CC} = 2.3 V to 2.7 V	1.7		.,
V_{IH}	High-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2		V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7 \times V_{CC}$		
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	
.,		V _{CC} = 2.3 V to 2.7 V		0.7	.,
V_{IL}	Low-level input voltage			0.8	V
				0.3 × V _{CC}	
٧ _I	Input voltage		0	5.5	V
٧o	Output voltage		0	Vcc	V
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
loL	Low-level output current	V 0V		16	mA
		V _{CC} = 3 V		24	
		V _{CC} = 4.5 V		32	
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V
		V _{CC} = 5 V ± 0.5 V		5	
TA	Operating free-air temperature		-40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER	TEST CO	VCC	MIN	TYP [†]	MAX	UNIT	
		I _{OL} = 100 μA		1.65 V to 5.5 V			0.1	
		I _{OL} = 4 mA		1.65 V			0.45	
		I _{OL} = 8 mA		2.3 V			0.3	
VOL		I _{OL} = 16 mA					0.4	V
		I _{OL} = 24 mA	3 V	0.55				
	I _{OL} = 32 mA			4.5 V			0.55	
II	A or B inputs	V _I = 5.5 V or GND		0 to 5.5 V			±1	μΑ
l _{off}		V_I or $V_O = 5.5 V$		0			±10	μΑ
Icc		V _I = 5.5 V or GND,	IO = 0	1.65 V to 5.5 V			10	μΑ
Δlcc	·	One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μΑ
Ci	·	V _I = V _{CC} or GND	_	3.3 V		4	·	pF
Co		$V_O = V_{CC}$ or GND		3.3 V		4.5		pF

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



SN74LVC2G38 DUAL 2-INPUT NAND GATE WITH OPEN DRAIN OUTPUT

SCES554A - MARCH 2004 - REVISED OCTOBER 2004

switching characteristics over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO	V _{CC} =		V _{CC} = ± 0.		V _{CC} = ± 0.	3.3 V 3 V	V _{CC} :		UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	2.5	8.5	1.5	5.2	1.3	4	0.9	3	ns

switching characteristics over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted) (see Figure 2)

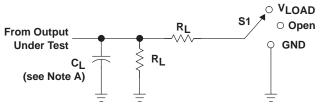
PARAMETER	FROM (INPUT)	то	V _{CC} =			2.5 V 2 V	V _{CC} = ± 0.		V _{CC} :		UNIT
	(INPUT)	(OUTPUT)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Υ	2.8	10	1.6	6	1.4	4.5	1	3.9	ns

operating characteristics, $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	LINUT
	PARAMETER TEST CON		TYP	TYP	TYP	TYP	UNIT
C_{pd}	Power dissipation capacitance	f = 10 MHz	6	7	7	9	pF



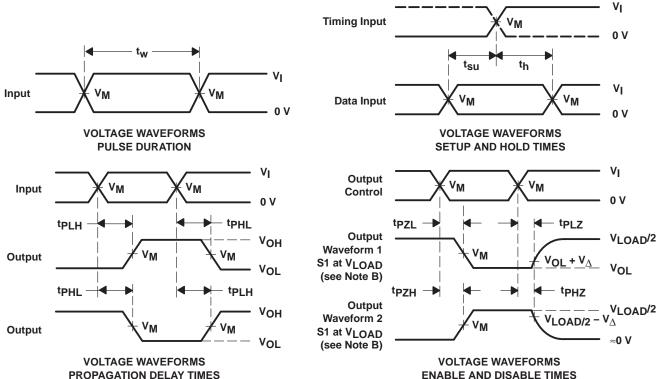
PARAMETER MEASUREMENT INFORMATION (OPEN DRAIN)



TEST	S1
tpZL (see Notes E and F)	VLOAD
tpLZ (see Notes E and G)	VLOAD
t _{PHZ} /t _{PZH}	V _{LOAD}

LOAD CIRCUIT

	IN	IPUT			_		
Vcc	V _I	t _r /t _f	VM	VLOAD	СL	RL	$v_{\scriptscriptstyle\Delta}$
1.8 V ± 0.15 V	vcc	≤ 2 ns	V _{CC} /2	2×V _{CC}	15 pF	1 M Ω	0.15 V
2.5 V \pm 0.2 V	VCC	≤ 2 ns	V _{CC} /2	2×V _{CC}	15 pF	1 M Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤ 2.5 ns	1.5 V	6 V	15 pF	1 M Ω	0.3 V
5 V \pm 0.5 V	VCC	≤ 2.5 ns	V _{CC} /2	2×V _{CC}	15 pF	1ΜΩ	0.3 V



INVERTING AND NONINVERTING OUTPUTS

ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

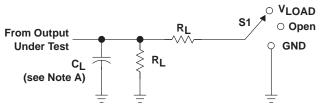
NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. Since this device has open-drain outputs, tpLZ and tpZL are the same as tpd.
- F. tpzi is measured at V_M.
- G. t_{PLZ} is measured at $V_{OL} + V_{\Lambda}$.
- H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION (OPEN DRAIN)

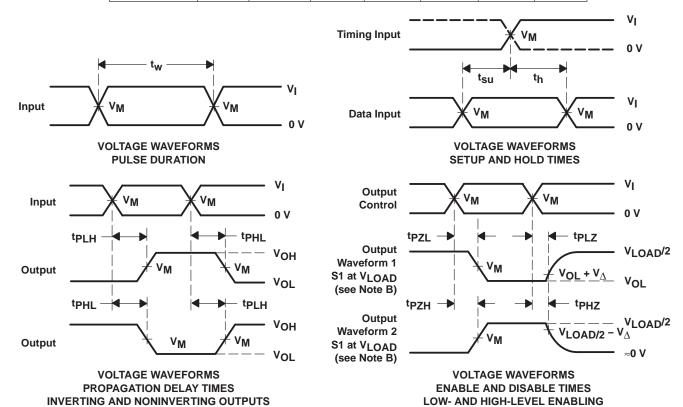


TEST	S1
tpzL (see Notes E and F)	VLOAD
t _{PLZ} (see Notes E and G)	VLOAD
tPHZ/tPZH	V_{LOAD}

LOW- AND HIGH-LEVEL ENABLING

LOAD CIRCUIT

	INPUT						
VCC	V _I	t _r /t _f	VM	VLOAD	СL	RL	$oldsymbol{V}_\Delta$
1.8 V ± 0.15 V	VCC	≤ 2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	VCC	≤ 2 ns	V _{CC} /2	2×V _{CC}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤ 2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	VCC	≤ 2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. Since this device has open-drain outputs, tpLZ and tpZL are the same as tpd.
- F. tpzi is measured at V_M.
- G. t_{PLZ} is measured at $V_{OL} + V_{\Lambda}$.
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms



DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

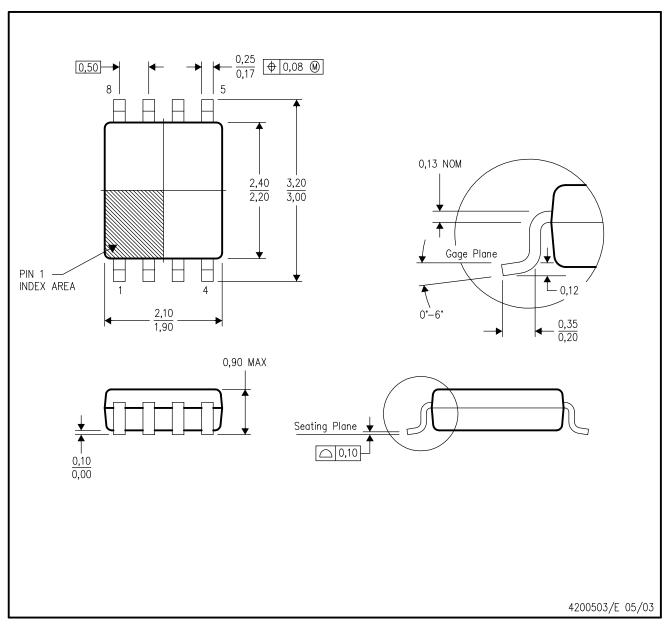


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



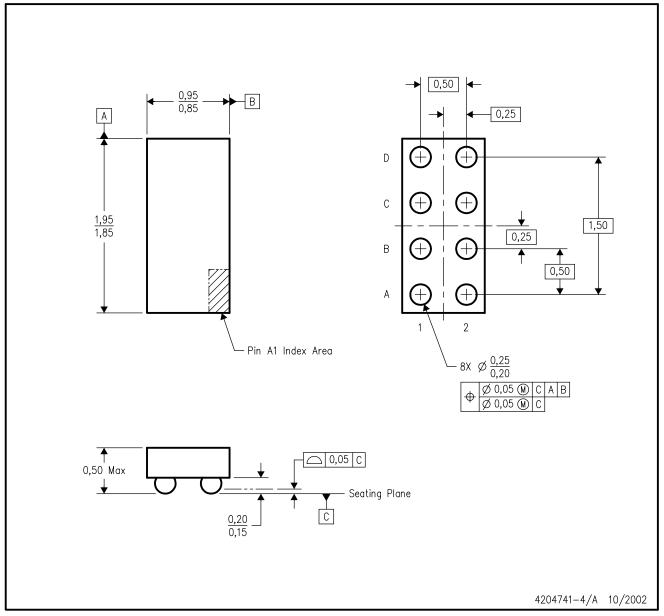
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation CA.



YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

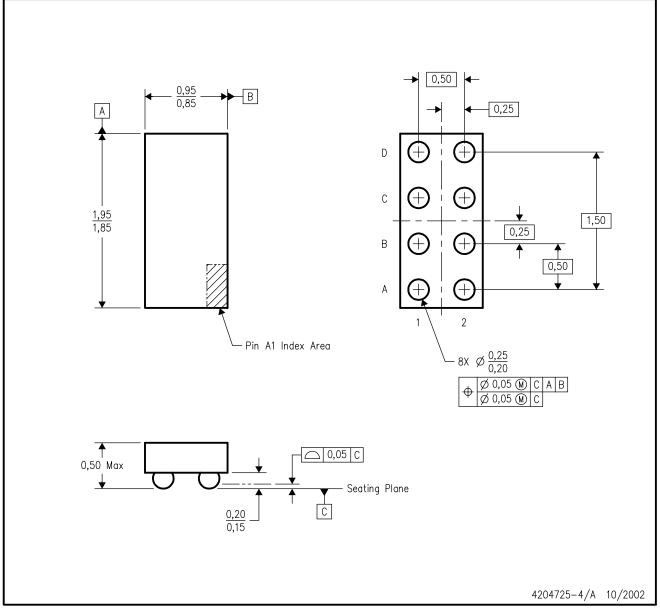
- B. This drawing is subject to change without notice.
- C. NanoFree $^{\text{TM}}$ package configuration.
- D. This package is lead-free. Refer to the 8 YEP package (drawing 4204725) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



YEP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar \mathbf{M} package configuration.
- D. This package is tin-lead (SnPb). Refer to the 8 YZP package (drawing 4204741) for lead-free.

NanoStar is a trademark of Texas Instruments.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Interface	interface.ti.com	Digital Control	www.ti.com/digitalcontrol
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
		Telephony	www.ti.com/telephony
		Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments

Post Office Box 655303 Dallas, Texas 75265

Copyright © 2004, Texas Instruments Incorporated

Copyright © Each Manufacturing Company.

All Datasheets cannot be modified without permission.

This datasheet has been download from:

www.AllDataSheet.com

100% Free DataSheet Search Site.

Free Download.

No Register.

Fast Search System.

www.AllDataSheet.com